

Monday, September 15

12:55-16:45 Short Course 1(313 & 314, 3rd Floor), Short Course 2 (Conference room 311 & 312, 3rd Floor)
17:00-18:00 Special Talk Session (Conference room 313+314, 3rd Floor)
18:00-19:30 Welcome Reception (Conference room 315, 3rd Floor)

Tuesday, September 16

9:00-11:45 Opening and Plenary Session (Conference room 301-304)											
Lunch											
Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
13:30-15:15	13:30-15:00	13:30-15:00	13:30-15:15	13:30-15:00	13:30-15:00	13:30-15:00	13:30-15:00	13:30-15:00	13:30-15:00	13:30-15:00	13:30-15:00
[A-1] CFET Technology	[B-1] 3D NAND Flash Memory	[C-1] Power and Sensing Circuits	[D-1] Spintronics/Quantum Materials/Reservoir Computing	[E-1] Photovoltaics	[F-1] Organic/Inorganic Hybrid Electronics	[G-1] Integrated Photonics	[H-1] Group IV Materials	[J-1] 3D Integration	[K-1] Growth	[M-1] SiC Materials and Processes	[N-1] Oxide Semiconductor Devices 1
Coffee break											
15:30-17:00	15:30-17:00	15:30-16:45		15:30-16:45	15:30-17:00	15:30-17:00	15:30-16:45	15:30-17:00	15:30-17:00	15:30-17:00	15:15-17:00
[A-2] Threshold Voltage Control	[B-2] In-Memory and Unconventional Computing 1	[C-2] Device Circuit Co-Design		[E-2] Thermoelectric Devices and Materials	[F-2] Organic Electronics	[G-2] Light Sources	[H-2] Wide Bandgap and Oxide Materials I	[J-2] Advanced Devices	[K-2] Characterization I	[M-2] THz and High-speed Devices	[N-2] Oxide Semiconductor Devices 2

Wednesday, September 17

Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
9:00-10:30	9:00-10:15				9:00-10:15	9:00-10:15	9:00-10:15	9:45-10:15	9:00-10:15	9:00-10:15	9:00-10:30
[A-3] Process Technology and Characterization	[B-3] Ferroelectric Devices				[F-3] Oscillators and Interface Circuits	[G-3] Advanced Photonic Designs	[H-3] Wide Bandgap and Oxide Materials II	[J-3] 3D Integration/Novel Materials	[K-3] Device I	[M-3] Ga203 Power Devices	[N-3] Oxide Semiconductor Devices 3
Coffee Break											
10:45-12:15	10:45-12:15			10:45-12:15	10:45-12:00	10:45-11:45	10:45-12:00	10:45-12:00	10:45-12:00	10:45-12:00	10:45-12:00
[A-4] Cryo CMOS and SOI Technology	[B-4] Ferroelectric Memory Devices			[E-4] ReRAM	[F-4] AI Computing Circuits	[G-4] UV Photonics	[H-4] Characterization and Device Applications	[J-4] 3D Integration/Packaging/Sensors/Novel Materials	[K-4] Characterization II	[M-4] GaN, Ga203 Processes	[N-4] Oxide Semiconductor Devices 4
Lunch											
13:30-14:00	13:30-14:32			13:30-13:42	13:30-13:56	13:30-14:10	14:00-14:28	14:15-14:31	13:30-14:12	13:30-14:20	13:30-14:10
[SO-PS-01] Short Oral Presentation	[SO-PS-02] Short Oral Presentation			[SO-PS-06] Short Oral Presentation	[SO-PS-07] Short Oral Presentation	[SO-PS-05] Short Oral Presentation	[SO-PS-11] Short Oral Presentation	[SO-PS-03] Short Oral Presentation	[SO-PS-08] Short Oral Presentation	[SO-PS-04] Short Oral Presentation	[SO-PS-10] Short Oral Presentation
				14:14-14:30	14:15-14:35						
				[SO-PS-09] Short Oral Presentation	[SO-PS-12] Short Oral Presentation						
Coffee Break											

Thursday, September 18

Room A (301, 3rd Floor)	Room B (302, 3rd Floor)	Room C (303, 3rd Floor)	Room D (304, 3rd Floor)	Room E (311, 3rd Floor)	Room F (312, 3rd Floor)	Room G (313, 3rd Floor)	Room H (314, 3rd Floor)	Room J (411+412, 4th Floor)	Room K (413, 4th Floor)	Room M (414+415, 4th Floor)	Room N (416+417, 4th Floor)
9:00-10:30	9:00-10:15			9:00-10:30	9:00-10:15	9:00-10:00	9:00-10:15	9:00-10:15	9:00-10:15	9:00-10:15	09:00-10:00
[A-5] CFET Technology and Self-heating	[B-5] Ferroelectric FET			[E-5] Qubit Technology	[F-5] Highly Sensitive Devices for Chem/Bio Detection 1	[G-5] Photonic Computing	[H-5] Low Dimensional Materials I	[J-5] In-Memory and Unconventional Computing 2	[K-5] Device II	[M-5] Emerging Materials and Devices	[N-5] Ferroelectric Memories and Gate Stack
Coffee Break											
10:45-12:00	10:45-12:15			10:45-12:00	10:45-12:00	10:45-11:45	10:45-11:45	10:45-12:15	10:45-11:45	10:45-12:00	10:15-12:15
[A-6] Integration Technology on Si Wafer	[B-6] Emerging Memory Devices, and DRAM			[E-6] Qubit Systems	[F-6] Highly Sensitive Devices for Chem/Bio Detection 2	[G-6] Materials for Photodetector	[H-6] Low Dimensional Materials II	[J-6] Emerging Memory Devices, and DRAM	[K-6] Characterization III	[M-6] III-V High-frequency and Power Devices	[N-6] Group-IV, III-V based Thin-film Growth, and Device Application
Lunch											
13:30-14:45	13:30-14:45			13:30-14:45	13:30-14:45		13:30-14:45		13:30-14:30	13:30-14:45	
[A-7] 2D Material Integration	[B-7] Ferroelectric Materials			[E-7] Energy Related Materials	[F-7] Bio/Medical Electronics		[H-7] Advanced Materials and Thin Films		[K-7] Device III	[M-7] Technologies for GaN HEMTs	
Coffee Break											
15:15-16:15	15:15-16:30								15:15-16:00	15:15-16:30	
[A-8] Vertical FET and New Devices	[B-8] Ferroelectric Memory Materials								[K-8] Device IV	[M-8] Si Materials and Devices	

Area Scope	Area 1: Advanced CMOS: Material Science / Process Engineering / Device Technology
	Area 2: Advanced and Emerging Memories / New Applications
	Area 3: Heterogeneous and 3D Integration / Interconnect / MEMS
	Area 4: Power / High-speed Devices and Materials
	Area 5: Photonics: Devices / Integration / Related Technology
	Area 6: Energy Harvesting and Converting Devices and Materials

Area Scope	Area 7: Organic / Molecular / Bio-electronics
	Area 8: Low Dimensional Devices and Materials
	Area 9: Novel Functional / Quantum / Spintronic Devices and Materials
	Area 10: Thin Film Electronics: Oxide / Non-single Crystalline / Novel Process
	Area 11: Advanced Materials: Synthesis / Crystal Growth / Characterization
	Area12: Advanced and Innovative Circuits / Systems Interacting with Innovative Devices and Materials